

RJH60D3DPE

Silicon N Channel IGBT Application: Inverter

REJ03G1844-0100 Rev.1.00 Oct 14, 2009

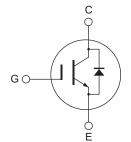
Features

- High breakdown-voltage
- Low on-voltage
- Built-in diode

Outline

RENESAS Package code: PRSS0004AE-B (Package name: LDPAK (S)-(1))





- 1. Gate
- 2. Collector
- 3. Emitter
- 4. Collecotor

Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Collector to emitter voltage / diode reverse voltage		600	V
Gate to emitter voltage		±30	V
Tc = 25°C	Ic	30	Α
Tc = 100°C	Ic	15	Α
Collector peak current		60	Α
Collector to emitter diode forward current		15	Α
Collector to emitter diode forward peak current		60	Α
Collector dissipation		120	W
Junction to case thermal impedance		1.04	°C/W
Junction temperature		150	°C
Storage temperature		-55 to +150	°C
	Tc = 25°C Tc = 100°C forward current forward peak current	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

2. Value at Tc = 25°C

RJH60D3DPE Preliminary

Electrical Characteristics

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 $I_F = 15 A$

 $di_F/dt = 100 A/\mu s$

ns

 $(Ta = 25^{\circ}C)$

ltem	Symbol	Min	Тур	Max	Unit	Test Conditions
Zero gate voltage collector current / Diode reverse current	I _{CES} / I _R	_	_	100	μА	V _{CE} = 600 V, V _{GE} = 0
Gate to emitter leak current	I _{GES}	_	_	±1	μΑ	$V_{GE} = \pm 30 \text{ V}, V_{CE} = 0$
Gate to emitter cutoff voltage	$V_{GE(off)}$	4.0	_	6.0	V	V _{CE} = 10 V, I _C = 1 mA
Collector to emitter saturation voltage	V _{CE(sat)}	_	1.6	2.2	V	$I_C = 15 \text{ A}, V_{GE} = 15 \text{ V}^{\text{Note3}}$
	V _{CE(sat)}	_	1.8	_	V	$I_C = 30A$, $V_{GE} = 15 V^{Note3}$
Input capacitance	Cies	_	900	_	pF	V _{CE} = 25 V
Output capacitance	Coes	_	50	_	pF	V _{GE} = 0
Reveres transfer capacitance	Cres	_	30	_	pF	f = 1 MHz
Total gate charge	Qg	_	35	_	nC	V _{GE} = 15 V
Gate to emitter charge	Qge	_	7	_	nC	V _{CE} = 300 V
Gate to collector charge	Qgc	_	20	_	nC	I _C = 15 A
Switching time	t _{d(on)}	_	40	_	ns	I _C = 15 A
	t _r	_	45	_	ns	$R_L = 20 \Omega$
	t _{d(off)}	_	60	_	ns	V _{GE} = 15 V
	t _f	_	100	_	ns	$Rg = 5 \Omega$
FRD Forward voltage	V _F		1.8	2.3	V	I _F = 15 A ^{Note3}

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Notes: 3. Pulse test.

FRD reverse recovery time

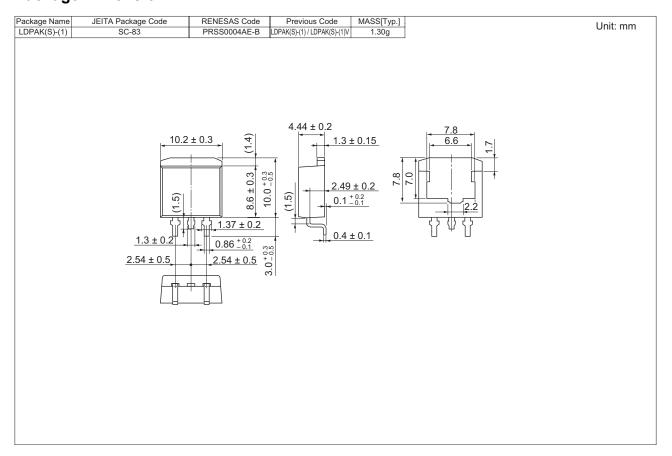
4. Under development — The specifications potentially be changed without notice.

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Package Dimension

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Ordering Information

Part No.	Quantity	Shipping Container
RJH60D3DPE-00-J3	1000 pcs	Taping

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- Notes:

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